B05 The thermal conductance at the interfaces of diamond, silicon, or germanium crystals and a copper heat sink with a gallium-indium eutectic as the heat transfer medium

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A liquid gallium-indium eutectic has been extensively used in the synchrotron radiation community to improve thermal contact at solid-solid interfaces and also as a strain-free mount for crystal monochromators. However no direct information exists on the extent of the thermal contact resistance between the optics and the heat sink when liquid gallium-indium eutectic is used as a heat transfer medium. This quantity may be important in predicting the performance of crystal optics for high-heat-load applications. So, in order to provide quantitative data, we performed a series of measurements of the heat transfer coefficient across the joints between a copper heat sink and diamond, silicon, or germanium single crystals with liquid gallium-indium eutectic at the interface. A simple steady-state method was used and the measurements were done under vacuum. The experimental method will be described, and the results of the conductance measurements will be presented.

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